

Customer No.: 31561
Application No.: 10/709,372
Docket NO.: 12409-US-PA

In The Specification:

Please amend paragraph [0031] as follows:

[0031] The composite dielectric layer 210 is formed between the gate 208 and the surface of the trench 202, and between the gate 208 and the substrate 200. The composite dielectric layer 210 includes at least a bottom dielectric layer 210a, a charge-trapping layer 210b and a cap dielectric layer 210c. The bottom dielectric layer 210a is fabricated using a silicon oxide material, for example. The bottom dielectric layer 210a mainly serves as a tunneling dielectric layer. Similarly, the cap dielectric layer 210c is fabricated using silicon oxide material, for example. The cap dielectric layer 210c serves as an insulation layer between the charge-trapping layer 210b and the gate 208. Obviously, the bottom dielectric layer 210a and the cap dielectric layer 210c may also be fabricated using some other dielectric materials. The charge-trapping layer ~~201b-210b~~ is fabricated using silicon nitride material, for example. However, the charge-trapping layer 210b can be fabricated using other material capable of trapping electric charges, such as, tantalum oxide, strontium titanate and hafnium oxide.